# **General Purpose Transistor**

## **NPN Silicon**

#### **Features**

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V <sub>CEO</sub>	45	Vdc
Collector - Base Voltage	V <sub>CBO</sub>	50	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	5.0	Vdc
Collector Current – Continuous	Ic	100	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board, (Note 1) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1.  $FR-5 = 1.0 \times 0.75 \times 0.062$  in.
- 2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

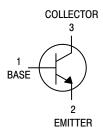


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SOT-23 (TO-236) CASE 318-08 STYLE 6



#### **MARKING DIAGRAM**



K2 = Device Code

M = Date Code\*

= Pb–Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
BCW72LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SBCW72LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

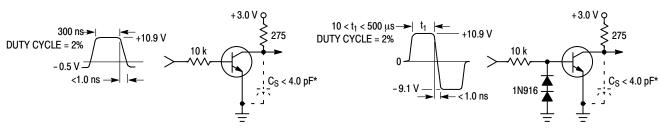
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## $\textbf{ELECTRICAL CHARACTERISTICS} \ (T_A = 25^{\circ}C \ unless \ otherwise \ noted)$

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage $(I_C = 2.0 \text{ mAdc}, V_{EB} = 0)$	V <sub>(BR)CEO</sub>	45	_	_	Vdc
Collector – Emitter Breakdown Voltage $(I_C = 2.0 \text{ mAdc}, V_{EB} = 0)$	V <sub>(BR)CES</sub>	45	_	_	Vdc
Collector – Base Breakdown Voltage $(I_C = 10 \mu Adc, I_E = 0)$	V <sub>(BR)CBO</sub>	50	_	_	Vdc
Emitter – Base Breakdown Voltage $(I_E = 10 \mu Adc, I_C = 0)$	V <sub>(BR)EBO</sub>	5.0	_	_	Vdc
Collector Cutoff Current $(V_{CB} = 20 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 20 \text{ Vdc}, I_E = 0, T_A = 100^{\circ}\text{C})$	Ісво	- -	_ _	100 10	nAdc μAdc
ON CHARACTERISTICS				-	
DC Current Gain (I <sub>C</sub> = 2.0 mAdc, V <sub>CE</sub> = 5.0 Vdc)	h <sub>FE</sub>	200	_	450	-
Collector – Emitter Saturation Voltage ( $I_C = 10 \text{ mAdc}$ , $I_B = 0.5 \text{ mAdc}$ ) ( $I_C = 50 \text{ mAdc}$ , $I_B = 2.5 \text{ mAdc}$ )	V <sub>CE(sat)</sub>	- -	_ 0.21	0.25 -	Vdc
Base – Emitter Saturation Voltage ( $I_C = 50 \text{ mAdc}$ , $I_B = 2.5 \text{ mAdc}$ )	V <sub>BE(sat)</sub>	-	0.85	_	Vdc
Base – Emitter On Voltage ( $I_C = 2.0 \text{ mAdc}$ , $V_{CE} = 5.0 \text{ Vdc}$ )	V <sub>BE(on)</sub>	0.6	_	0.75	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product (I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 5.0 Vdc, f = 100 MHz)	f <sub>T</sub>	-	300	_	MHz
Output Capacitance ( $I_E = 0$ , $V_{CB} = 10$ Vdc, $f = 1.0$ MHz)	C <sub>obo</sub>	-	_	4.0	pF
Input Capacitance ( $I_E = 0$ , $V_{CB} = 10$ Vdc, $f = 1.0$ MHz)	C <sub>ibo</sub>	-	9.0	_	pF
Noise Figure (I <sub>C</sub> = 0.2 mAdc, $V_{CE}$ = 5.0 Vdc, $R_S$ = 2.0 k $\Omega$ , f = 1.0 kHz, BW = 200 Hz)	NF	-	_	10	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

#### **EQUIVALENT SWITCHING TIME TEST CIRCUITS**



\*Total shunt capacitance of test jig and connectors

Figure 1. Turn-On Time

Figure 2. Turn-Off Time

#### **TYPICAL NOISE CHARACTERISTICS**

 $(V_{CE} = 5.0 \text{ Vdc}, T_A = 25^{\circ}\text{C})$ 

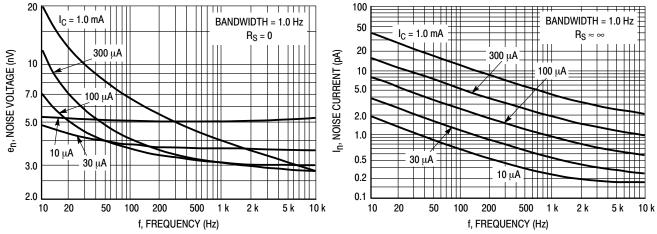


Figure 3. Noise Voltage

Figure 4. Noise Current

#### **NOISE FIGURE CONTOURS**

 $(V_{CE} = 5.0 \text{ Vdc}, T_A = 25^{\circ}C)$ 

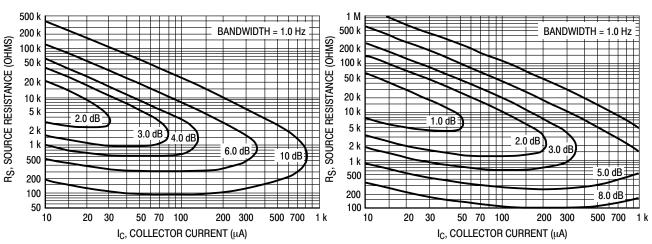


Figure 5. Narrow Band, 100 Hz

Figure 6. Narrow Band, 1.0 kHz

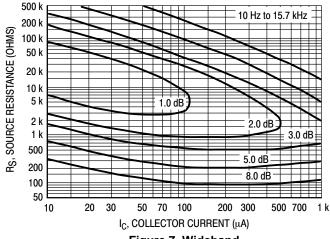


Figure 7. Wideband

Noise Figure is defined as:

$$NF = 20 \log_{10} \left( \frac{e_n^2 + 4KTR_S + I_n^2 R_S^2}{4KTR_S} \right)^{1/2}$$

e<sub>n</sub> = Noise Voltage of the Transistor referred to the input. (Figure 3)

I<sub>n</sub> = Noise Current of the Transistor referred to the input. (Figure 4)

K = Boltzman's Constant (1.38 x  $10^{-23}$  j/°K)

T = Temperature of the Source Resistance (°K)

R<sub>S</sub> = Source Resistance (Ohms)

#### **TYPICAL STATIC CHARACTERISTICS**

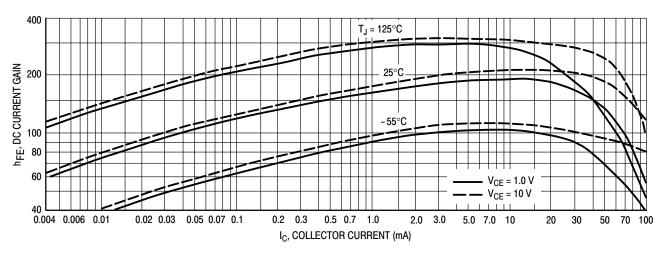


Figure 8. DC Current Gain

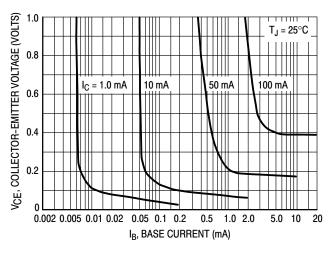


Figure 9. Collector Saturation Region

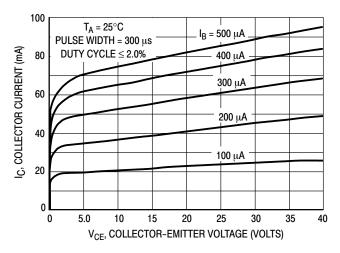


Figure 10. Collector Characteristics

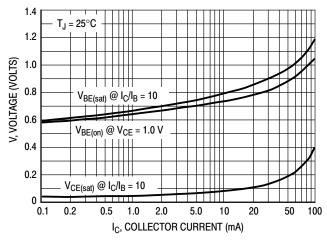


Figure 11. "On" Voltages

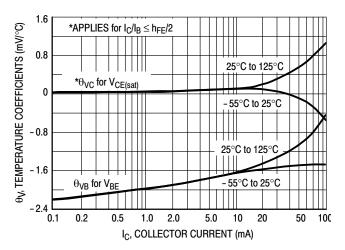


Figure 12. Temperature Coefficients

#### TYPICAL DYNAMIC CHARACTERISTICS

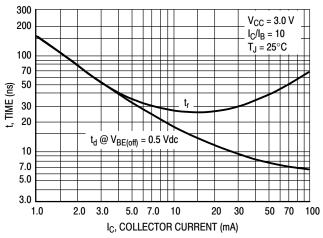


Figure 13. Turn-On Time

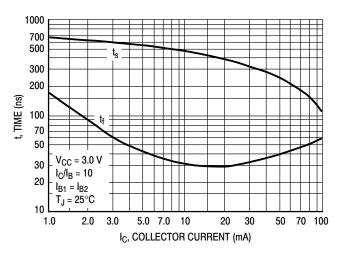


Figure 14. Turn-Off Time

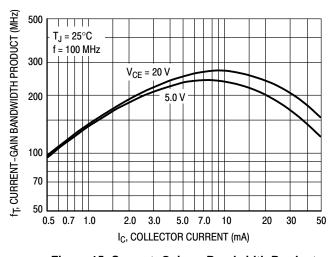


Figure 15. Current-Gain — Bandwidth Product

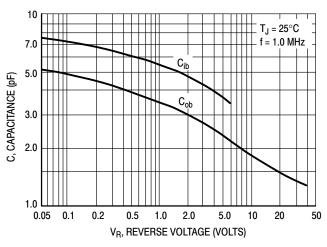


Figure 16. Capacitance

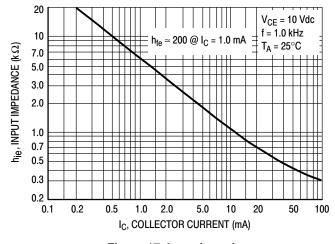


Figure 17. Input Impedance

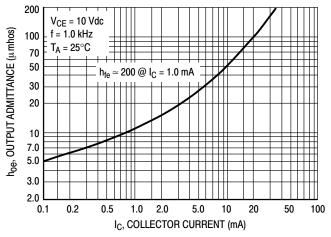


Figure 18. Output Admittance

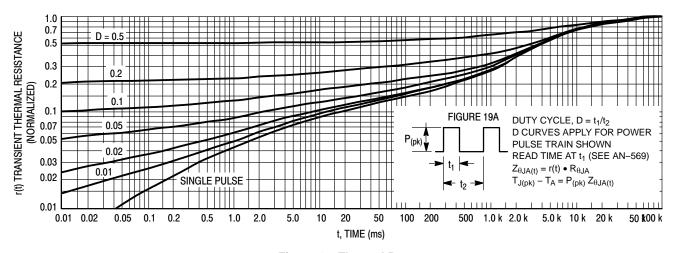


Figure 19. Thermal Response

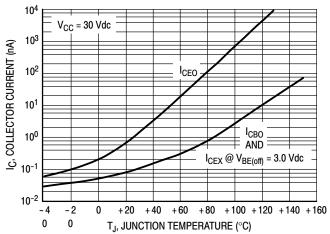


Figure 19A.

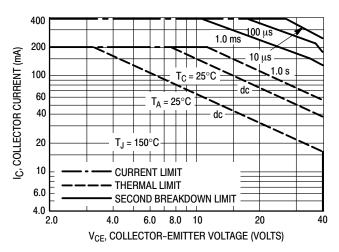


Figure 20.

#### **DESIGN NOTE: USE OF THERMAL RESPONSE DATA**

A train of periodical power pulses can be represented by the model as shown in Figure 19A. Using the model and the device thermal response the normalized effective transient thermal resistance of Figure 19 was calculated for various duty cycles.

To find  $Z_{\theta JA(t)},$  multiply the value obtained from Figure 19 by the steady state value  $R_{\theta JA}.$ 

Example:

The MPS3904 is dissipating 2.0 watts peak under the following conditions:

 $t_1 = 1.0 \text{ ms}, t_2 = 5.0 \text{ ms}. (D = 0.2)$ 

Using Figure 19 at a pulse width of 1.0 ms and D = 0.2, the reading of r(t) is 0.22.

The peak rise in junction temperature is therefore

 $\Delta T = r(t) \times P_{(pk)} \times R_{\theta JA} = 0.22 \times 2.0 \times 200 = 88^{\circ}C.$ 

For more information, see AN-569.

The safe operating area curves indicate  $I_C-V_{CE}$  limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 20 is based upon  $T_{J(pk)}=150^{\circ}C$ ;  $T_{C}$  or  $T_{A}$  is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided  $T_{J(pk)} \leq 150^{\circ}C$ .  $T_{J(pk)}$  may be calculated from the data in Figure 19. At high case or ambient temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.



SOT-23 (TO-236) CASE 318-08 **ISSUE AS** 

**DATE 30 JAN 2018** 

# SCALE 4:1 D - 3X b

**TOP VIEW** 







#### **RECOMMENDED SOLDERING FOOTPRINT**



DIMENSIONS: MILLIMETERS

#### NOTES:

- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
  MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,

	PROT	RUSIONS, OR GATE BURRS.	
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	MILLIMETERS				INCHES	
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0°		10°	0°		10°

#### **GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code

= Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE
OT (1 F O			

SOT-23 (TO-236)

STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
<ol><li>ANODE</li></ol>	<ol><li>SOURCE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	2. DRAIN	2. GATE
<ol><li>CATHODE</li></ol>	3. GATE	<ol><li>CATHODE-ANODE</li></ol>	<ol><li>ANODE</li></ol>	3. GATE	<ol><li>ANODE</li></ol>

STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	2. ANODE	<ol><li>CATHODE</li></ol>	2. ANODE	<ol><li>ANODE</li></ol>
<ol><li>ANODE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>ANODE</li></ol>	<ol><li>CATHODE-ANOD</li></ol>	E 3. GATE

STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
<ol><li>SOURCE</li></ol>	<ol><li>OUTPUT</li></ol>	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3 DRAIN	3 INPLIT	3 CATHODE	3. SOURCE	3. GATE	<ol><li>NO CONNECTION</li></ol>

STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE	
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